

METHOD OF FORMING HIGH ASPECT RATIO STRUCTURES

ABSTRACT OF THE DISCLOSURE

An etching process includes providing a dielectric first film on a substrate
5 and a sacrificial second film on the dielectric first film. A conductive structure such
as a container capacitor is formed in a recess in the first and second films. The
conductive structure is exposed as to its external surface by an etch process that
resists destructive collapse of the conductive structure.

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